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(54) **OPTICAL DISK PROTECTIVE FILM AND
SPUTTERING TARGET FOR FORMATION OF
THAT PROTECTIVE FILM**

(57) Abstract:

PROBLEM TO BE SOLVED: To permit DC sputtering, to decrease the production of particles to increase the production efficiency, and to provide a protective film having large transmittance and low reflectance by using a sputtering target essentially comprising ZnO and if necessary by adding other oxides.

SOLUTION: The sputtering target for the formation of

an protective film of an optical disk is produced by sintering one or more oxides of ZnO, In₂O₃ and SnO₂ as the main component with addition of Al₂O₃ or Ga₂O₃ if necessary by 0.1 to 20 wt.%. The content of Al₂O₃ and Ga₂O₃ is preferably controlled to 0.1 to 20 wt.%, and thereby, the bulk electric resistance of the target can be controlled and the transmittance in the visible ray region of the protective film after the protective film is formed can be maintained to $\geq 80\%$. Further, ZrO₂ and/or TiO₂ are incorporated by 0.01 to 5 wt.%.

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